

## FDMA430NZ

### Single N-Channel 2.5V Specified PowerTrench® MOSFET

**30V, 5.0A, 40mΩ**

#### General Description

This Single N-Channel MOSFET has been designed using Fairchild Semiconductor's advanced Power Trench process to optimize the  $R_{DS(on)}$  @  $V_{GS}=2.5V$  on special MicroFET leadframe.

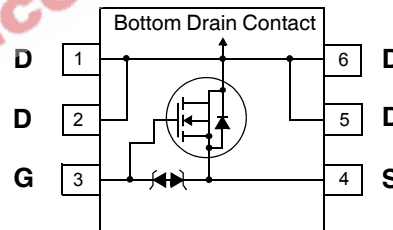
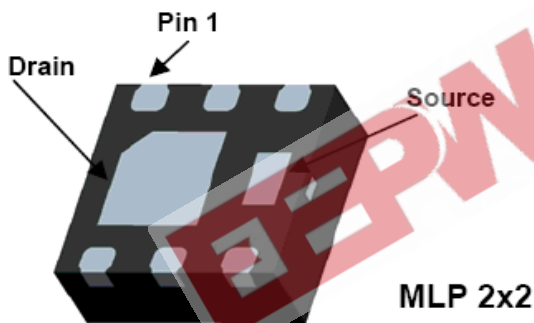
#### Applications

- Li-Ion Battery Pack



#### Features

- $R_{DS(on)} = 40m\Omega$  @  $V_{GS} = 4.5 V, I_D = 5.0 A$
- $R_{DS(on)} = 50m\Omega$  @  $V_{GS} = 2.5 V, I_D = 4.5 A$
- Low Profile-0.8mm maximum-in the new package MicroFET 2x2 mm
- RoHS Compliant



#### Absolute Maximum Ratings $T_A = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DSS}$	Drain-Source Voltage	30	V
$V_{GSS}$	Gate-Source Voltage	$\pm 12$	V
$I_D$	Drain Current -Continuous (Note 1a) -Pulsed	5.0	A
		20	
$P_D$	Power dissipation (Steady State) (Note 1a) (Note 1b)	0.9	W
		2.4	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ C$

#### Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	145	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1b)	52	

#### Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
430	FDMA430NZ	7"	12mm	3000 units

**Electrical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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**Off Characteristics**

$B_{VDSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	30			V
$\frac{\Delta B_{VDSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu A$ , Referenced to $25^\circ\text{C}$		25.2		$\text{mV}/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 24V, V_{GS} = 0V$ ,			1	$\mu A$
$I_{GSS}$	Gate-Body Leakage,	$V_{GS} = \pm 12V, V_{DS} = 0V$			$\pm 10$	$\mu A$

**On Characteristics** (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.6	0.81	1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250\mu A$ , Referenced to $25^\circ\text{C}$		-3.2		$\text{mV}/^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 4.5V, I_D = 5.0A$		23.6	40	$\text{m}\Omega$
		$V_{GS} = 4.0V, I_D = 5.0A$		23.9	41	
		$V_{GS} = 3.1V, I_D = 4.5A$		25.4	43	
		$V_{GS} = 2.5V, I_D = 4.5A$		27.6	50	
		$V_{GS} = 4.5V, I_D = 5.0A$ , $T_J = 150^\circ\text{C}$		37.0	61	
$g_{FS}$	Forward Transconductance	$V_{DS} = 5V, I_D = 5.0A$		25.6		S

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = 10V, V_{GS} = 0V$ , $f = 1.0\text{MHz}$		600	800	$\text{pF}$
$C_{oss}$	Output Capacitance			110	150	$\text{pF}$
$C_{rss}$	Reverse Transfer Capacitance			75	115	$\text{pF}$
$R_G$	Gate Resistance			3.5		$\Omega$

**Switching Characteristics** (Note 2)

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 10V, I_D = 1A$ $V_{GS} = 4.5V, R_{GEN} = 6\Omega$		8.3	17	ns
$t_r$	Turn-On Rise Time			7.1	15	ns
$t_{d(off)}$	Turn-Off Delay Time			18.1	37	ns
$t_f$	Turn-Off Fall Time			6.0	12	ns
$Q_g$	Total Gate Charge	$V_{DS} = 10V, I_D = 5.0A$ , $V_{GS} = 4.5V$		7.3	11	nC
$Q_{gs}$	Gate-Source Charge			0.8	2	nC
$Q_{gd}$	Gate-Drain Charge			1.9	3	nC

**Drain-Source Diode Characteristics and Maximum Ratings**

$I_S$	Maximum Continuous Drain-Source Diode Forward Current			2.0	A	
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0V, I_S = 2.0A$		0.69	1.2	V
$t_{rr}$	Diode Reverse Recovery Time	$I_F = 5.0A$ , $di/dt = 100A/\mu s$			17	ns
$Q_{rr}$	Diode Reverse Recovery Charge				5	nC

**Notes:**

- $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.
  - $145^\circ\text{C}/\text{W}$  when mounted on a minimum pad of 2 oz copper
  - $52^\circ\text{C}/\text{W}$  when mounted on a  $1\text{ in}^2$  pad of 2 oz copper
- Pulse Test: Pulse Width < 300  $\mu s$ , Duty Cycle < 2.0%
- The diode connected between the gate and the source serves only as protection against ESD. No gate overvoltage rating is implied.

**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

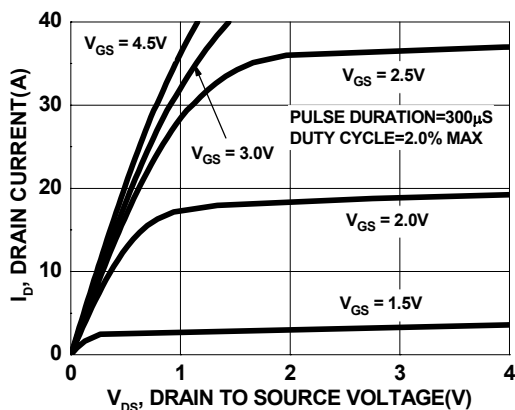


Figure 1. On Region Characteristics

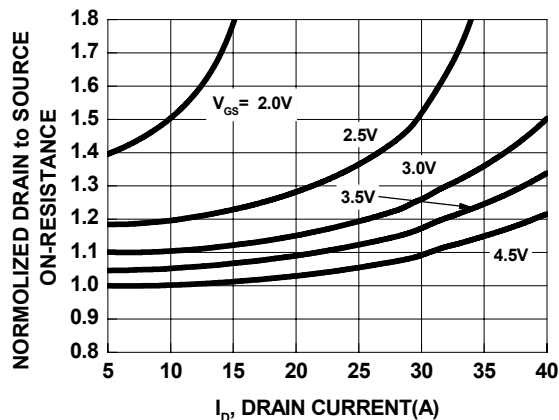


Figure 2. On-Resistance vs Drain Current and Gate Voltage

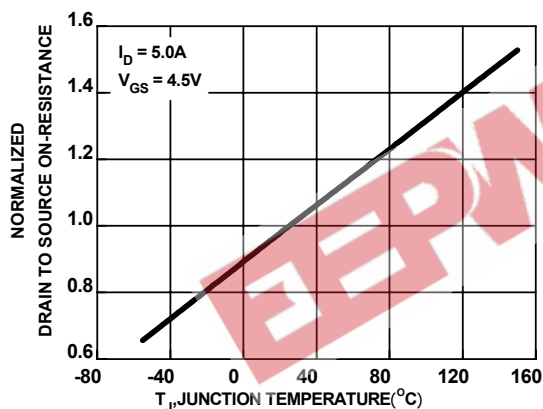


Figure 3. Normalized On Resistance vs Junction Temperature

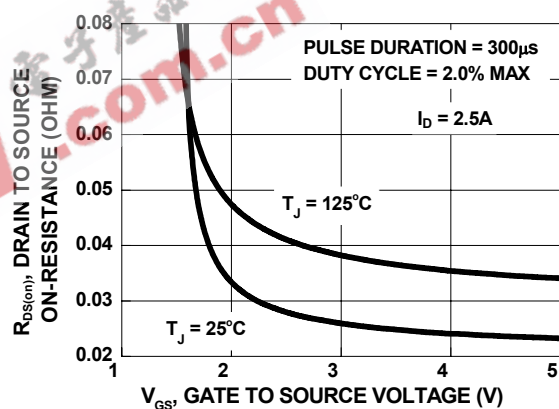


Figure 4. On-Resistance vs Gate to Source Voltage

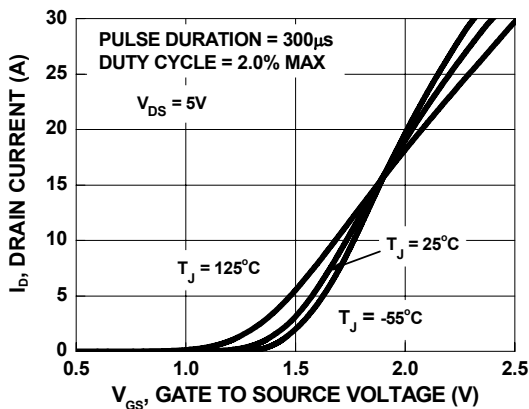


Figure 5. Transfer Characteristics

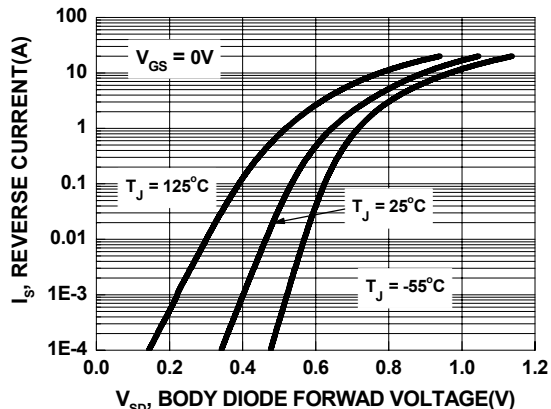


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

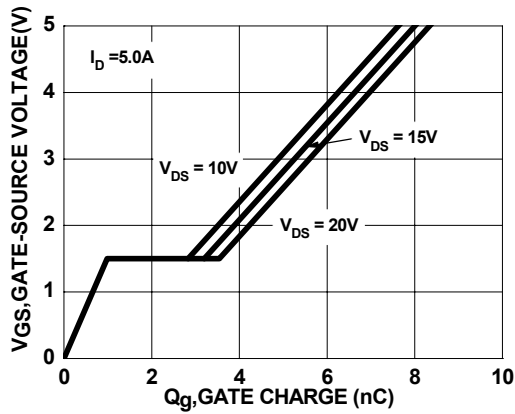


Figure 7. Gate Charge Characteristics

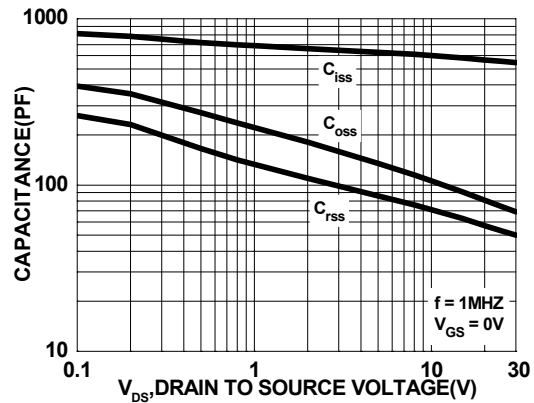


Figure 8. Capacitance vs Drain to Source Voltage

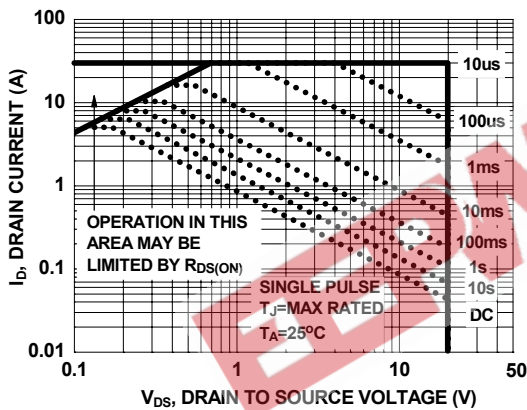


Figure 9. Safe Operating Area

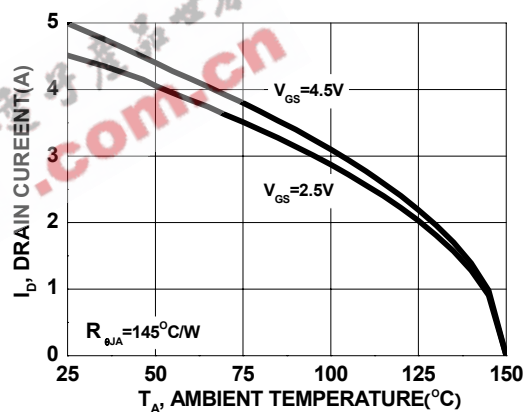


Figure 10. Maximum Continuous Drain Current vs Ambient Temperature

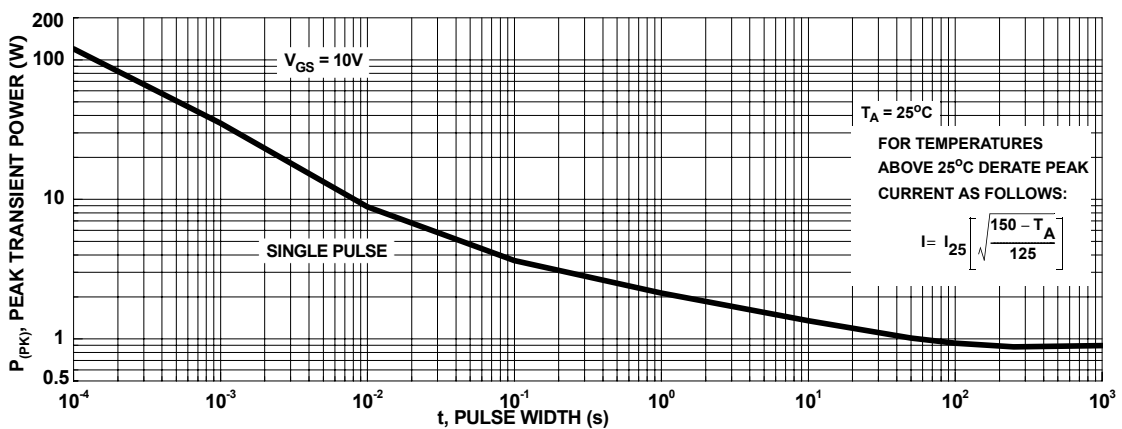


Figure 11. Single Pulse Maximum Power Dissipation

**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

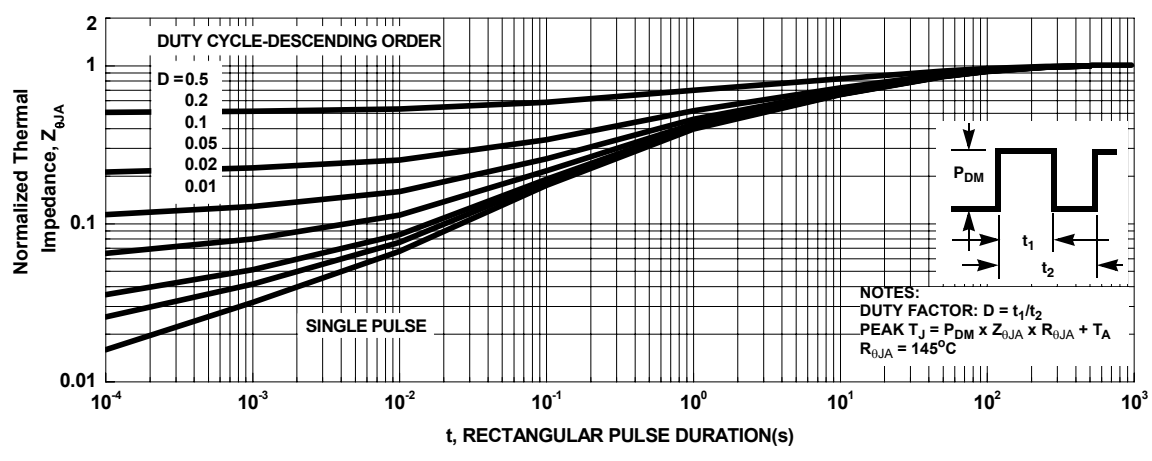
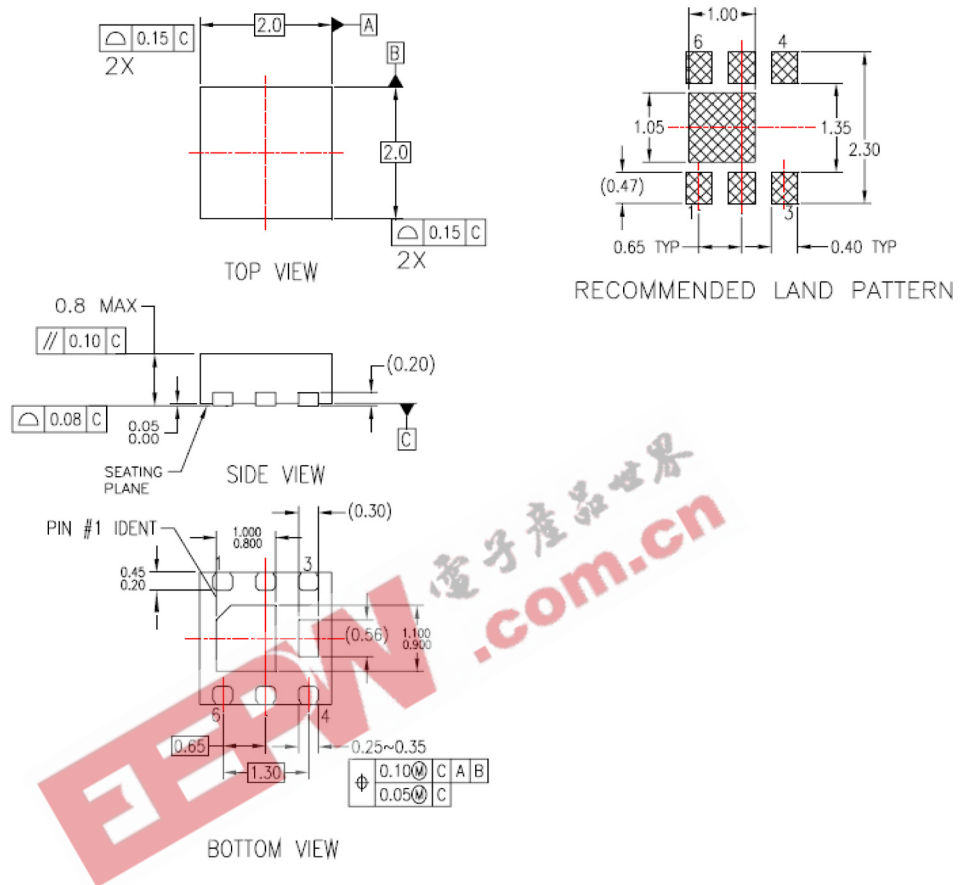


Figure 12. Transient Thermal Response Curve



Dimensional Outline and Pad Layout



- NOTES:
- A. NOT FULLY CONFORM TO JEDEC REGISTRATION MO-229 DATED AUG/2003.
  - B. DIMENSIONS ARE IN MILLIMETERS.
  - C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994

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